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1AP20 REGISTRATION 06 JAN 2006

Docket No.: 20506/0203830-US0
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

**In re Patent Application of:
Euijoon Yoon et al.**

Application No.: Not Yet Assigned

Confirmation No.: N/A

Filed: Concurrently Herewith

Art Unit: N/A

For: GROWTH METHOD FOR NITRIDE
SEMICONDUCTOR EPITAXIAL LAYERS

Examiner: Not Yet Assigned

CLAIM FOR PRIORITY AND SUBMISSION OF DOCUMENTS

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Applicant hereby claims priority under 35 U.S.C. 119 based on the following prior foreign application filed in the following foreign country on the date indicated:

| | | |
|-------------------|-----------------|--------------|
| Country | Application No. | Date |
| Republic of Korea | 10-2003-0046119 | July 8, 2003 |

A certified copy of the aforesaid Korean Patent Application was received by the International Bureau on July 26, 2004 during the pendency of International Application No. PCT/KR2004/001665. A copy of Form PCT/IB/304 is enclosed.

Dated: January 6, 2006

Respectfully submitted,

By _____

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